


PRELIMINARY
 Notice: This is not a final specification.
 Some parametric limits are subject to change.

MITSUBISHI Nch POWER MOSFET

FY8BCH-02F

HIGH-SPEED SWITCHING USE

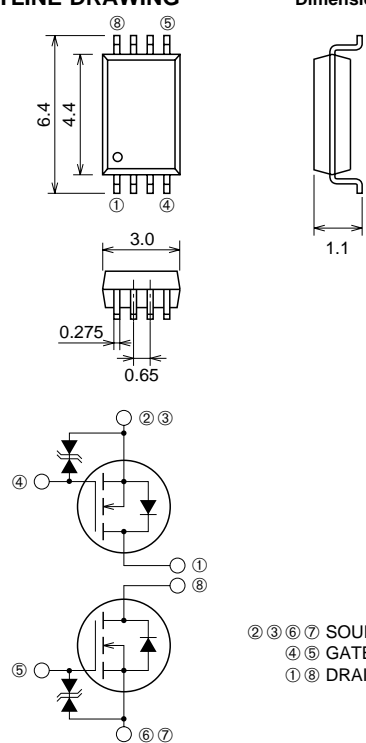
FY8BCH-02F



- 2.5V DRIVE
- V_{DSS} 20V
- $r_{DS(ON)}$ (MAX) 16m Ω
- I_D 8A

OUTLINE DRAWING

Dimensions in mm



② ③ ⑥ ⑦ SOURCE
 ④ ⑤ GATE
 ① ⑧ DRAIN

TSSOP8

APPLICATION

Li - ion battery protection

MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-source voltage	$V_{GS} = 0V$	20	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	± 10	V
I_D	Drain current		8	A
I_{DM}	Drain current (Pulsed)		56	A
I_{DA}	Avalanche current (Pulsed)	$L = 10\mu H$	8	A
I_S	Source current		1.5	A
I_{SM}	Source current (Pulsed)		6.0	A
P_D	Maximum power dissipation		1.6	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	0.035	g

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ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	20	—	—	V
V (BR) GSS	Gate-source breakdown voltage	I _G = ±100μA, V _{DS} = 0V	±10	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±10V, V _{DS} = 0V	—	—	±10	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 20V, V _{GS} = 0V	—	—	0.1	mA
V _{GS} (th)	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	0.5	0.9	1.5	V
r _{DS} (ON)	Drain-source on-state resistance	I _D = 8A, V _{GS} = 4V	—	13	16	mΩ
r _{DS} (ON)	Drain-source on-state resistance	I _D = 4A, V _{GS} = 2.5V	—	17	22	mΩ
V _{DS} (ON)	Drain-source on-state voltage	I _D = 8A, V _{GS} = 4V	—	0.104	0.128	V
y _{fs}	Forward transfer admittance	I _D = 8A, V _{DS} = 10V	—	—	—	S
C _{iss}	Input capacitance	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz	—	1800	—	pF
C _{oss}	Output capacitance		—	—	—	pF
C _{rss}	Reverse transfer capacitance		—	—	—	pF
t _d (on)	Turn-on delay time	V _{DD} = 10V, I _D = 4A, V _{GS} = 4V, R _{GEN} = R _{GS} = 50Ω	—	—	—	ns
t _r	Rise time		—	—	—	ns
t _d (off)	Turn-off delay time		—	—	—	ns
t _f	Fall time		—	—	—	ns
V _{SD}	Source-drain voltage	I _S = 1.5A, V _{GS} = 0V	—	0.85	1.1	V
R _{th} (ch-a)	Thermal resistance	Channel to ambient	—	—	78.1	°C/W
t _{rr}	Reverse recovery time	I _S = 1.5A, dis/dt = -50A/μs	—	50	—	ns